
Advanced Gate Stack, Source/Drain, and Channel Engineering for Si-Based CMOS 4: New Materials, Processes, and Equipment

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Sponsoring Divisions:



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Dielectric Science & Technology



High Temperature Materials



Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™

Vol. 13 No. 1

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA
Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)

ISBN 978-1-56677-626-4

Printed in the United States of America.

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